



骏业（香港）实业有限公司

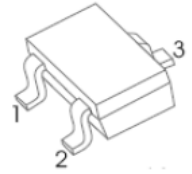
400-0744-078

SOT-323 Plastic-Encapsulate Transistors

SS8050

TRANSISTOR (NPN)

SOT-323



1. BASE
2. EMITTER
3. COLLECTOR

FEATURES

Complimentary to SS8550

MARKING: Y1

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	40	V
V_{CE0}	Collector-Emitter Voltage	25	V
V_{EB0}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1.5	A
P_C	Collector Power Dissipation	0.25	W
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1\text{mA}$, $I_B=0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$, $I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=40\text{V}$, $I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CB}=20\text{V}$, $I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}$, $I_C=100\text{mA}$	120		400	
	$h_{FE(2)}$	$V_{CE}=1\text{V}$, $I_C=800\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=800\text{mA}$, $I_B=80\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=800\text{mA}$, $I_B=80\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE}=10\text{V}$, $I_C=50\text{mA}$, $f=30\text{MHz}$	100			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}$, $I_E=0$, $f=1\text{MHz}$			15	pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	L	H	J
Range	120-200	200-350	300-400

Typical Characterisitics

SS8050

